Effect of Thickness on Optical Properties of Nickel Oxide Thin Films

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Abstract: A thin film of Nickel Oxide (263.15, 144.9, and 90.9) nm was deposited on an FTO glass substrate using the spin coating process. Absorption coefficient, extinction coefficient, refractive index, and optical energy gap were determined using absorbance spectra collected with a UV-VIS spectrophotometer. The absorbance spectrum of all samples ranges from 200 to 400 nm, and absorbance increases with thickness, with a high absorbance value at 236 nm corresponding to photon energy 5.254 eV. The absorption coefficient ranges between 1.9×10^7 and 8.6×10^6 cm-1 for all samples. As the thickness decreases, the value increases, indicating a direct electronic transition. The maximum refractive index for all samples is 1.0222. The obtained optical energy gap value is between (3.526 and 3.358) eV, and the optical band gap decreases as the thickness of the thin film increases.

Keyword: Nickel Oxide, Thin Films, Refractive Index, absorption coefficient and optical energy gap.

Introduction

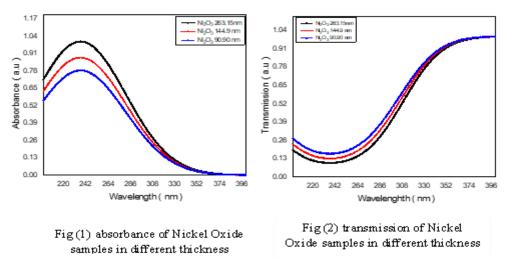
A thin film is a layer that extends endlessly in two dimensions but is constrained in the third direction, with a thickness ranging from several nanometers to a few micrometers [1]. Thin film cells have been popular since the late 1970s, when solar calculators powered by a thin strip of amorphous silicon were introduced to the market. It is now available in big modules for application in sophisticated building integrated installations and vehicle charging systems [2, 3]. Thin films have numerous advantages, including size reduction, adjustment of material surface properties (reflection, absorption, hardness, abrasion resistance, corrosion, and electrical behavior), cost savings, and device miniaturization [4,5]. Thin Film Deposition technology is often recognized as the primary key to the development of electronics such as computers, as all microelectronic solid-state devices are built on material structures generated by deposition techniques. Thin film technology is distinguished by excellent stability and accuracy of electronic components and devices, as well as a level of reliability that is not economically attainable with other technologies [6].

Nickel oxide (NiO) is a desirable substance because of its chemical stability [7]. It is a semiconductor with cubic crystal structure. NiO has a wide inherent band gap of around 3.6 eV [8]. It exhibits remarkable optical, electrical, and magnetic properties. It is a viable candidate for a variety of applications, including smart windows, gas sensors, catalysts, anode materials in Li-ion batteries, and nanoscale optoelectronic devices such as electrochromic displays [9]. Furthermore, nanocrystalline NiO powder exhibits super paramagnetism, which can be employed as a medication delivery and MRI (magnetic resonance imaging) agent. NiO nanostructures have been synthesized using a variety of processes, including sol-gel, co-precipitation, hydrothermal, solvothermal, anodic arc plasma, sonochemical, microwave pyrolysis, thermal decomposition, micro-emulsion, and chemical precipitation. In this study, the optical characteristics of nickel oxide generated via sol-gel technique were investigated using a UV-VIS spectrometer.

Method

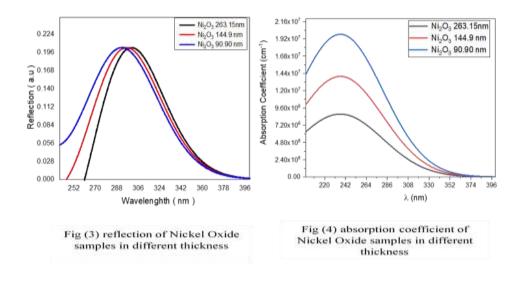
Nickel oxide thin films were prepared by spraying a 0.1 M solution of nickel nitrate of doubly distilled water onto the pre-heated amorphous glass substrates kept at $(390^{\circ}C \pm 10^{\circ})$ C. Iron oxide thin films were prepared by spraying a 0.1 M solution of ferric nitrate of doubly distilled water onto the pre-heated amorphous glass substrates kept at $(390^{\circ}C \pm 10^{\circ})$ C. Film thickness was measured by using the weight difference method considering the substrate surface area and the density of the bulk nickel oxide. As the density of thin films was certainly lower than the bulk density, the actual film thickness would be larger than the estimated values the thickness of the thin film. The optical characterization of the prepared thin films was calculated from absorbance spectrum that obtained using UV-VIS spectrometer.

Results and Discussion



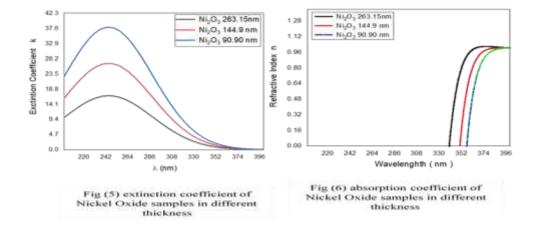
The absorbance spectrum of nickel oxide thin film samples in different thickness (263.15, 144.9 and 90.9) nm were obtained using UV-VS min 1240 spectrophotometer and then used to calculate some optical properties.

Figure (1) depicts the absorbance results of nickel oxide thin film samples; the absorbance curve shows a rapid increase in absorption at wavelengths 236 nm, with a photon energy of 5.254 eV, as thickness increases in the UV area. The transmission is the opposite behavior of absorbance; the transmissions of all samples of Ni_3O_2 were as shown in fig (2); it was noticed that the transmissions value increases when the thickness decreases.



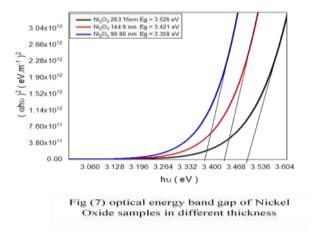
International Journal of Engineering and Information Systems (IJEAIS) ISSN: 2643-640X Vol. 8 Issue 2 February - 2024, Pages: 13-16

Figure 3 shows the reflection for nickel oxide thin film samples. The greatest reflection value spanned from 290nm to 305nm, with a blue shift as thickness decreased, and the samples became mirrors in this range. The absorption coefficient (α) of nickel oxide thin film samples was calculated using the equation $\alpha = ((2.303 \times A))/t$, where (A) is absorbance and (t) is optical length in the samples [11]. Fig (4) The plot of (α) with wavelength (λ) shows that the value of $\alpha = 1.9 \times 10^7$ cm⁻¹ for Ni₂O₃ (90.9 nm) thin film thickness samples at 236 nm when the Ni₂O₃ (144.9 nm) thin film thickness sample equal 1.4×10^7 cm⁻¹ at the same wavelength, but the Ni₂O₃ (263.15) nm thin film thickness sample equal 8.6×10^6 cm⁻¹ at the same wavelength. This means that the transition must correspond to direct electronic transition, and the properties of this state are important. Additionally, the value of (α) for nickel oxide thin film samples increased while thickness samples declined.



Extinction coefficient (K) was calculated using the related $k = \frac{\alpha \lambda}{4\pi}$ [12]. The variation at the (K) values as a function of (λ) are shown in fig (5) for nickel oxide thin film samples, the obtained value of (K) at the 236 nm wavelength was depend on the samples thickness, the value of (K) for Ni₂O₃ (90.9 nm) thin film thickness sample equal 38 while for Ni₂O₃ (144.9 nm) thin film thickness sample equal 27 and for Ni₂O₃ (263.15 nm) thin film thickness sample equal 17, the extinction coefficient (k) decreased when the thickness increased . The refractive index (n) is the relative between speeds of light in vacuum to its speed in material which does

not absorb this light. The value of n was calculated from the equation $n = \left[\left(\frac{1+R}{1-R}\right)^2 - (1+k^2)\right]^{\frac{1}{2}} + \frac{(1+R)}{(1-R)}$ Where (R) is the reflectivity [13], the variation of (n) vs. (λ) is shown in fig (6) which shows that the maximum value of (n) is (1.0222) for Ni₂O₃ (263.15nm) at wavelength (273nm).



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The optical energy gap (Eg) has been calculated by the relation $(\alpha h \upsilon)^2 = C(h \upsilon - Eg)$ where (C) is constant[14]. By plotting $(\alpha h \upsilon)^2$ vs photon energy (h υ) as shown in fig.(7) for all samples of Ni₂O₃ thin films . And by extrapolating the straight thin portion of the curve to intercept the energy axis, the value of the energy gap has been obtained, from fig (7) the obtained value of (Eg) equals 3.526 eV for Ni₂O₃ (263.15 nm) while for Ni₂O₃ (144.9 nm) equal 3.421 eV and equal3.358 eV for Ni₂O₃ (90.90 nm), It is clear that the optical band gap decreases as the thickness of the thin film increases.

Conclusion

The thickness of nickel oxide thin films has a clear impact on optical properties (absorbance, transmission, reflection, absorption coefficient, extinction coefficient, and optical energy gap). All optical properties calculated for wavelengths ranging from 200 to 400 nm. According to the results, these thin film samples are suited for photoelectric applications.

References

[1] Thomas M.Chirstensen, Understanding Surface and Film Science, 1st edition, CRC Press 2022, ISBN 1482233037.

[2] Dongfang Yang, Th in Films Deposition, Methods and Applications, IntechOpen, 2023, ISBN 978-1-80356-457-9.

[3] Zexian Cao, Thin Film Growth Physics, Materials Science and Technology, Elsevier Science, 2016, ISBN 9780081017227.

[4] Safwa Abdalla, Abdelsakhi Sulima, Yousif Alsabah, Abdelrahman Elbadawi, Khalid Mohammed Haroun, Thin Film Gum Arabic Doping by Potassium Bromide Solar Cells, Volume 7, Issue 2, 2020.

[5] Oleksii Diachenko, Jaroslav Kováč, Jr., Oleksandr Dobrozhan, Patrik Novák, Jaroslav Kováč, Jaroslava Skriniarova and Anatoliy Opanasyuk, Structural and Optical Properties of CuO Thin Films Synthesized Using Spray Pyrolysis Method, MDPI, Coatings 2021, DOI: <u>https://doi.org/10.3390/coatings1111392</u>.

[6] Sawicka-Chudy, P.; Sibi ´nski, M.; Rybak-Wilusz, E.; Cholewa, M.;Wisz, G.; Yavorskyi, R. Review of the development of copper oxides with titanium dioxide thin-film solar cells. AIP Adv. 2020, 10, 010701.

[7] M. P. Deshpande, Kiran N. Patel, Vivek P. Gujarati, Kamakshi Patel, S. H. Chaki, Structural, Thermal and Optical Properties of Nickel Oxide (NiO) Nanoparticles Synthesized by Chemical Precipitation Method, Advanced Materials Research, 2016, Vol. 1141, doi:10.4028/www.scientific.net/AMR.1141.65.

[8] Ekane Peter Etape, Oga Eugene Agbor, Beckley Victorine Namondo, Zoubir Benmaamar, Josepha Foba-Tendo1, John Ngolui Lambi, Synthesis, Characterization, and Effects of Morphology on the Magnetic Application Base Properties of Pure Nickel Oxide (NiO) and Cobalt-Doped Nickel Oxide/Nickel Hydroxide ($Co_xNi_{1-x}O/Ni(OH)_2$) Nanocomposites, Advances in Nanoparticles, 2023, 12,DOI: https://doi.org/10.4236/anp.2023.123009.

[9] I. Ngom, · N. M. Ndiaye, · N. F. Sylla, · S. Dieng, B. D. Ngom, M. Maaza, Study of the physical properties of NiO nanoparticles synthesized from the flowers, seeds, and leaves extracts of Moringa oleifera, MRS Advances, 2023, DOI: https://doi.org/10.1557/s43580-023-00578-2.

[10] Mohsin, M.H., Haider, M.J., Al-Shibaany, Z.Y.A, et al, Synthesis of Nio/sI Using Sol-Gel as A Photosensor, Silicon, 2022, DOI: https://doi.org/10.1007/s12633-020-00872.

[11] Salma Fath Alrahman Ahmed, Khalid Mohamed Haroun, Adam Mohammed Adam Bakheet, Yousif Hassan Alsheikh, Abdalsakhi Suliman, Study of the Optical Properties of Isonitrosoacetophenone (C_8H7NO2) Using UV-Vis Spectroscopy, Journal of Photonic Materials and Technology, 2019; 5(2): 32-37, DOI:10.11648/j.jmpt.20190502.12.

[12] Yousef A. Alsabah, Abdelrahman A. Elbadawi, Rania M. Abaker, Abdelsakhi Suliman & Hassan H. Abuelhassan, Optical properties and efficiency studies for Beta Vulgarize, Curcuma Longa and Vulgaris var. cicla dye sensitized solar cell, International Journal of Engineering and Applied Physics (IJEAP), Vol. 2, No. 3, September 2022, ISSN: 2737-8071.

[13] Rawia Abd-alaziez1, Aldesogi Omer hamed, Mohammed Elmubark, Omaima Elrayah, Abdalsakhi, S.M.H, Abdel Karim Sabir Ali, Quantitative Optical Properties of Acacia tortilis var. raddiana Gum using Ultra Violet Visible "UV- VI" Spectrophotometer, Neelain Journal of Science and Technology NJST volume 5, Issue 2, December 2021.

[14] Ibtehag Ali Sanosy, Khalid Mohammed. Haroun, Abdalsakhi Suliman Mohammed Hamed, Adam Mohammed Adam Bakheet - Optical Properties of Barium Borate (BaB₂O₄) Compound for Current Optoelectronic Applications - Journal of Materials & Metallurgical Engineering ISSN: 2231-3818 (Online), ISSN: 2321-4236 (Print) Volume 10, Issue 1 www.stmjournals.com; 10(1), 2020.